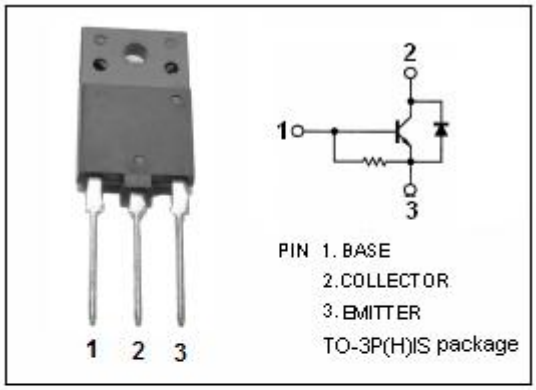
# isc Silicon NPN Power Transistor 2SC5517

## DESCRIPTION

- High Breakdown Voltage-
  : $V_{CBO}$= 1700V (Min)
- High Switching Speed
- Wide Area of Safe Operation
- Built-in Damper Diode
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

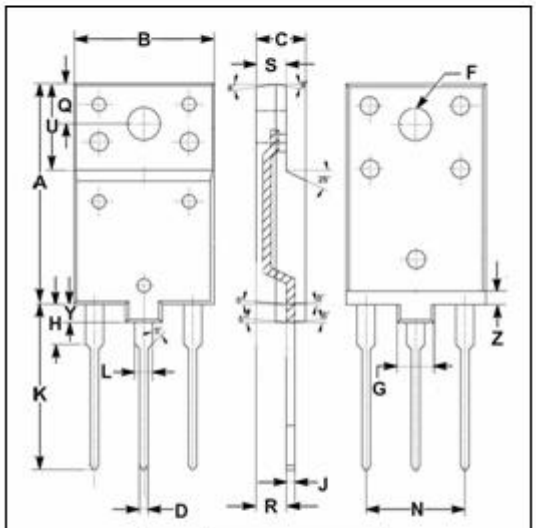



## APPLICATIONS

- Designed for horizontal deflection output applications

## ABSOLUTE MAXIMUM RATINGS($T_a$=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT |
|---|---|---|---|
| $V_{CBO}$ | Collector-Base Voltage | 1700 | V |
| $V_{CES}$ | Collector-Emitter Voltage | 1700 | V |
| $V_{EBO}$ | Emitter-Base Voltage | 7 | V |
| $I_C$ | Collector Current- Continuous | 6 | A |
| $I_{CM}$ | Collector Current- Peak | 12 | A |
| $I_B$ | Base Current- Continuous | 3 | A |
| $P_C$ | Collector Power Dissipation @ $T_a$=25℃ | 3 | W |
| | Collector Power Dissipation @ $T_C$=25℃ | 40 | |
| $T_J$ | Junction Temperature | 150 | ℃ |
| $T_{stg}$ | Storage Temperature Range | -55~150 | ℃ |




| DIM | mm MIN | mm MAX |
|---|---|---|
| A | 24.10 | 24.70 |
| B | 15.20 | 15.80 |
| C | 5.20 | 5.80 |
| D | 0.65 | 1.05 |
| F | 3.30 | 3.90 |
| G | 3.90 | 4.10 |
| H | 4.30 | 4.70 |
| J | 0.80 | 1.00 |
| K | 18.30 | 18.70 |
| L | 1.90 | 2.40 |
| N | 10.70 | 11.10 |
| Q | 4.40 | 4.60 |
| R | 3.30 | 3.70 |
| S | 3.20 | 3.40 |
| U | 9.50 | 9.70 |
| Y | 1.90 | 2.10 |
| Z | 1.40 | 1.60 |

# isc Silicon NPN Power Transistor 2SC5517

## ELECTRICAL CHARACTERISTICS

**$T_C$=25℃ unless otherwise specified**

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|---|---|---|---|---|---|---|
| $V_{(BR)EBO}$ | Emitter-Base Breakdown Voltage | $I_E$= 500mA; $I_C$= 0 | 7 | | | V |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C$= 4.5A; $I_B$= 0.9A | | | 5.0 | V |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage | $I_C$= 4.5A; $I_B$= 0.9A | | | 1.5 | V |
| $I_{CBO}$ | Collector Cutoff Current | $V_{CB}$= 1000V; $I_E$= 0<br>$V_{CB}$= 1700V; $I_E$= 0 | | | 50<br>1.0 | μA<br>mA |
| $h_{FE}$ | DC Current Gain | $I_C$= 4.5A; $V_{CE}$= 5V | 5 | | 9 | |
| $f_T$ | Current-Gain—Bandwidth Product | $I_C$= 0.1A; $V_{CE}$= 10V | | 3 | | MHz |
| $V_{ECF}$ | C-E Diode Forward Voltage | $I_F$= 4.5A | | | 2.0 | V |
| Switching Times | | | | | | |
| $t_{stg}$ | Storage Time | $I_C$= 4.5A; $I_{B1}$= 0.9A; $I_{B2}$= -1.8A | | | 5.0 | μs |
| $t_f$ | Fall Time | | | | 0.5 | μs |

**NOTICE:**

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.